Ordering number: EN 3182B

SANYO

No.3182B

2SA1766

PNP Epitaxial Planar Silicon Transistor

High h_{FE}, Low-Frequency General-Purpose Amp Applications

Features

- . Adoption of FBET, MBIT processes
- . High DC current gain (h_{FE} = 500 to 1200)
- . Large current capacity
- · Low collector-to-emitter saturation voltage
- · High V_{EBO}

Absolute Maximum Ratings at Ta = 25°C

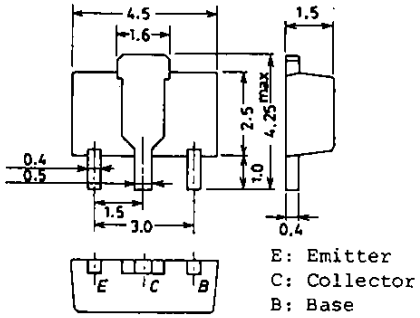
				unit
Collector to Base Voltage	V_{CBO}		−30	V
Collector to Emitter Voltage	V_{CEO}		−25	V
Emitter to Base Voltage	V_{EBO}		−15	V
Collector Current	I_C		−300	mA
Collector Current(Pulse)	I_{CP}		−500	mA
Base Current	I_B		−60	mA
Collector Dissipation	P_C	Mounted on ceramic board (250mm² × 0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = −20V, I_E = 0			−0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = −10V, I_C = 0			−0.1	μA
DC Current Gain	$h_{FE}(1)$	V_{CE} = −5V, I_C = −10mA	500	800	1200	
	$h_{FE}(2)$	V_{CE} = −5V, I_C = −200mA	200			
Gain-Bandwidth Product	f_T	V_{CE} = −10V, I_C = −10mA		100		MHz
Output Capacitance	c_{ob}	V_{CB} = −10V, f = 1MHz		12		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = −200mA, I_B = −4mA		−0.12	−0.50	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = −200mA, I_B = −4mA		−0.77	−1.10	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C = −10μA, I_E = 0	−30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C = −1mA, R_{BE} = ∞	−25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E = −10μA, I_C = 0	−15			V

Marking : AL

Package Dimensions 2038
(unit : mm)



E: Emitter
C: Collector
B: Base
SANYO: PCP
(Bottom View)

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